

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Dureseti CHIDAMBARRAO, et al. Group Art Unit: 2814
Appln. No. : 10/605,108 Examiner: PHAM, Long
Filed : September 9, 2003 Confirmation No. 2107
For : METHOD FOR REDUCED N+ DIFFUSION IN STRAINED SI
ON SI/GE SUBSTRATE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria, VA 22314
Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, and supplemental to the Information Disclosure Statement filed on August 25, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned. Copies of non-US patent documents as well as the documents listed in the "Other Documents" section of the attached PTO-1449 are enclosed.

Applicants respectfully request that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that this Information Disclosure Statement is being after receipt of a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, please charge the required fee of \$180.00 to **IBM Deposit Account No. 09-0458** (Fishkill).

Should the US Patent & Trademark Office conclude that other fees are required, authorization is hereby given to charge **IBM Deposit Account No. 09-0458** (Fishkill) any fee necessary to ensure consideration of these materials.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
Dureseti CHIDAMBARRAO, et al.

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', is written over a horizontal line.

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Reg. No. 38,093

May 15, 2006
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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030183US1		Application No. 10/605,108	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Dureseti CHIDAMBARRAO, et al.			
				Filing Date 09/09/2003		Group 2814	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							